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Unit in mm

查询"2SA1241O"供应商 TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

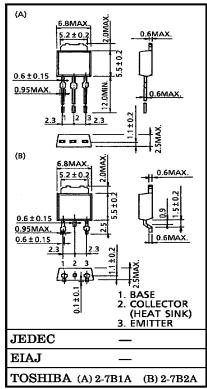
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POWER AMPLIFIER APPLICATIONS POWER SWITCHING APPLICATIONS

- Low Collector Saturation Voltage : $V_{CE (sat)} = -0.5 V (Max.) (I_C = -1 A)$
- Excellent Switching Time : $t_{stg} = 1.0 \ \mu s$ (Typ.)
- Complementary to 2SC3076

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERIST	SYMBOL	RATING	UNIT		
Collector-Base Voltage	V _{CBO} -50		V		
Collector-Emitter Voltage	VCEO	-50	v		
Emitter-Base Voltage		VEBO	-5	V	
Collector Current		IC	$^{-2}$	Α	
Base Current		IB	-1	Α	
Collector Power	$Ta = 25^{\circ}C$	Pa	1.0	w	
Dissipation	$Tc = 25^{\circ}C$	PC	10		
Junction Temperature		Tj	150	°C	
Storage Temperature Range		$\mathrm{T_{stg}}$	$-55 \sim 150$	°C	



Weight: 0.36 g

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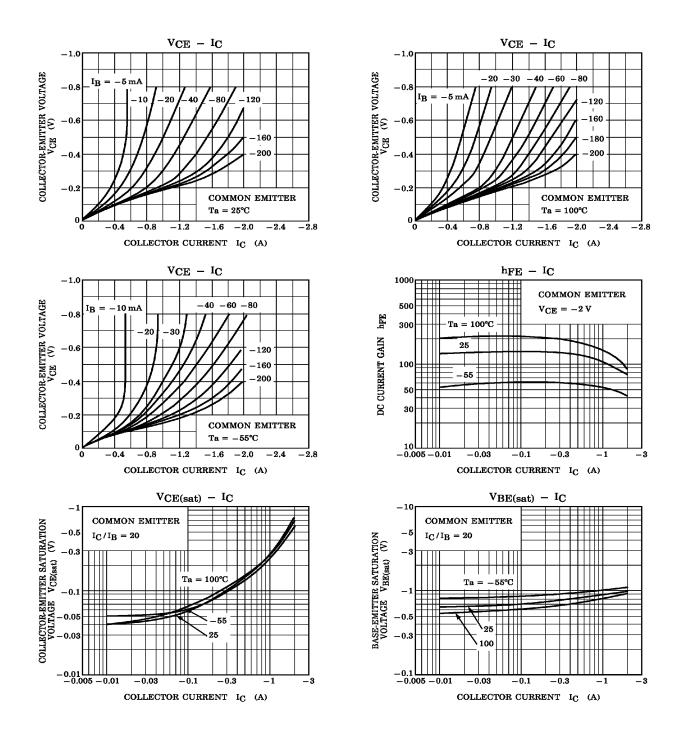
	IARACIERISTICS	$\frac{10 - 25 \text{ C}}{10 - 25 \text{ C}}$					
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	$V_{CB} = -50 V, I_E = 0$	_	—	-1.0	μA
Emitter Cut-off Current		IEBO	$V_{EB} = -5 V, I_{C} = 0$	_		-1.0	μA
Collector-Emitter Breakdown Voltage		V (BR) CEO	$I_{C} = -10 \text{ mA}, I_{B} = 0$	-50	_	_	v
DC Current Gain		h _{FE (1)} (Note)	$V_{CE} = -2 V$, $I_{C} = -0.5 A$	70	_	240	
		hFE (2)	$V_{CE} = -2 V, I_B = -1.5 A$	40	_	—	
Collector-Emit Saturation Vo		V _{CE (sat)}	$I_{C} = -1 A, I_{B} = -0.05 A$	_	_	-0.5	v
Base-Emitter Saturation Voltage		V _{BE (sat)}	$I_{C} = -1 A, I_{B} = -0.05 A$	_		-1.2	v
Transition Frequency		$\mathbf{f_{T}}$	$V_{CE} = -2 V, I_{C} = -0.5 A$	_	100	_	MHz
Collector Output Capacitance		C _{ob}		I	40	_	pF
Switching Time	Turn-on Time	ton		I	0.1	_	
	Storage Time	t _{stg}			1.0	_	μs
	Fall Time	tf	$-I_{B1} = I_{B2} = 0.05 \text{ A} V_{CC} = -30 \text{ V}$ DUTY CYCLE $\leq 1\%$	_	0.1	_	

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Note : $h_{FE(1)}$ Classification O : 70~140, Y : 120~240

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